

ABSTRACT

An optical semiconductor device comprises a semiconductor laser (11) including a lower clad layer, an active layer (4), and an upper layer formed in this order,
5 an electroabsorptive modulator (12) including the lower clad, a light absorption layer (6), and the upper clad layer formed in this order, and a separation region (13) provided between the semiconductor laser and the
10 electroabsorptive modulator. The upper clad layer extends from the semiconductor laser through the separation region to the electroabsorptive modulator and up to the side of the separation region.